

## Silicon Standard Recovery Diode

$V_{RRM} = 600\text{ V} - 1200\text{ V}$   
 $I_F = 150\text{ A}$

### Features

- High Surge Capability
- Types up to 1200 V  $V_{RRM}$

DO-8 Package



### Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	S150J (R)	S150K (R)	S150M (R)	S150Q (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		600	800	1000	1200	V
RMS reverse voltage	$V_{RMS}$		420	560	700	840	V
DC blocking voltage	$V_{DC}$		600	800	1000	1200	V
Continuous forward current	$I_F$	$T_C \leq 180\text{ °C}$	150	150	150	150	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	3140	3140	3140	3140	A
Operating temperature	$T_j$		-65 to 200	-65 to 200	-65 to 200	-65 to 200	°C
Storage temperature	$T_{stg}$		-65 to 200	-65 to 200	-65 to 200	-65 to 200	°C

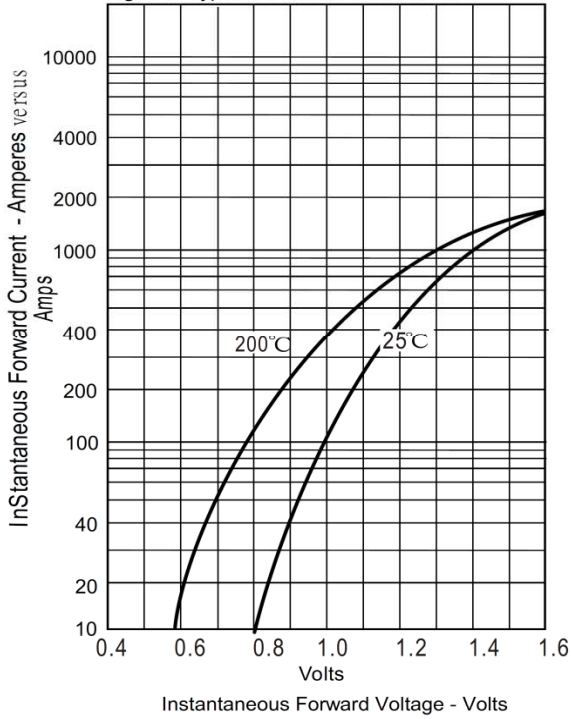
### Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	S150J (R)	S150K (R)	S150M (R)	S150Q (R)	Unit
Diode forward voltage	$V_F$	$I_F = 150\text{ A}$ , $T_j = 25\text{ °C}$	1.2	1.2	1.2	1.2	V
Reverse current	$I_R$	$V_R = 600\text{ V}$ , $T_j = 25\text{ °C}$	10	10	10	10	$\mu\text{A}$
		$V_R = 600\text{ V}$ , $T_j = 150\text{ °C}$	15	15	15	9	mA

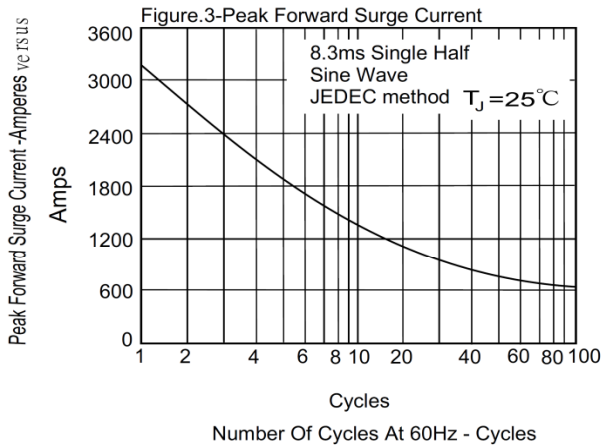
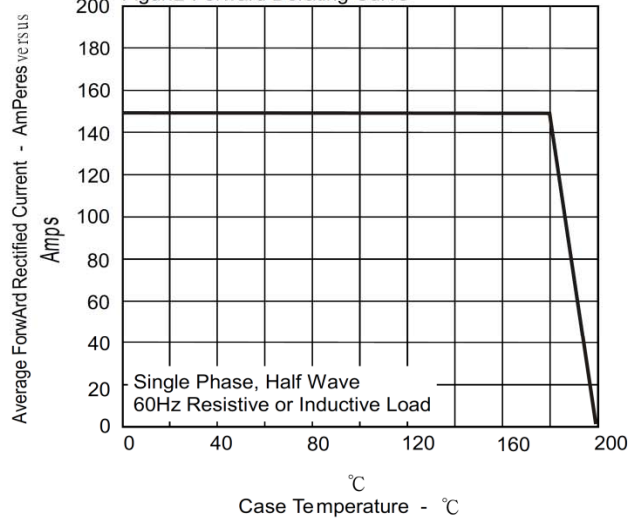
### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.35	0.35	0.35	0.35	°C/W
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Figure.1-Typical Forward Characteristics



Figur.2-Forward Derating Curve



Figur.4-Typical Reverse Characteristics

